

Submission under 37 C.F.R. §1.114  
Serial No. 10/623,679  
Attorney Docket No. 030891

**REMARKS**

Claims 1-3 and 5-30 are pending in this application. The amendment of claims 1, 21-23, 26 and 27, filed on October 10, 2006, was not entered. In this response, a Request for Reconsideration is herewith filed. Claims 29 and 30 have been also added in this response.

(1) Claims 1-3 and 5-28 were rejected under 35 U.S.C. §103(a) as being unpatentable over Ishibashi et al. (U.S. Patent No. 6,579,657) in view of Kanda et al. (JP2001-019860).

(i) Claims 1, 21, 23, 26 and 27 have been amended to delete the “alcohol surfactant” and “secondary alcohol ethoxylate surfactant.” The surfactants taught by Kanda et al. are an acetylene alcohol, an acetylene glycol, a polyethoxylate of an acetylene alcohol, and a polyethoxylate of an acetylene glycol. Kanda et al. do not teach or suggest the other surfactants. Please see the abstract and paragraphs [0009]-[0010]. Thus, even a combination of the cited references does not make the invention of the amended claims.

(ii) Claims 1, 21, 23, 26 and 27 have been also amended to incorporate the limitation of thickening the resist pattern formed of an ArF resist. The basis of the amendment is found at page 3, line 12 to page 6, line 10; page 37, last line 4 to 38, line 9; and etc.

None of the cited references teaches thickening a resist pattern formed by using an ArF resist. In Examples of Ishibashi et al., the resist patterns formed by using an i ray resist, a KrF

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resist and an EB resist (col. 12, line 55 to col. 14, line 16) were thickened. In Kanda et al., the resist patterns formed by using an i resist and a KrF resist were thickened (paragraphs [0023]-[0024]). There is no actual data disclosed in the cited references that the disclosed composition can be used for thickening a resist pattern formed by using an ArF resist. Neither of the cited references teaches a resist pattern thickening material for thickening a resist pattern formed by using an ArF resist.

In the Advisory Action dated October 26, 2006, the Examiner states that Ishibashi et al. teach employing ArF laser. However, there is no actual data for the ArF laser in Ishibashi et al. The invention of the composition for thickening a resist pattern formed of an ArF resist was not completed at the time when Ishibashi et al. was filed, at least because there is no actual reduction of the invention for the composition for thickening a resist pattern formed of an ArF resist. It is not obvious to one skilled in the art to modify the incomplete invention of Ishibashi et al. to complete by referring to the teachings of the second reference.

On the other hand, the material of the present invention, as specifically recited in the claims, can efficiently thicken the resist pattern formed of ArF resist, as shown in the description and Tables 1-3 at pages 37-41 of the specification.

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Thus, the present invention is unobvious over the cited references. Reconsideration of the rejection is respectfully requested.

(2) Claims 29 and 30 have been added. In Table 1 at page 37, the surfactant of the present invention is calculated to be 1.25 to 2.5 weight parts with respect to 100 parts of the resin. See Example B including KW-3 (20 weight parts) and NP-675 (0.25 weight parts); and Example C including KW-3 (10 weight parts) and SP-12 (0.25 weight parts).

In Example 1 of Kanda et al. ([0020]), the surfactant (2,4,7,9-tetramethyl-5-decyl-4,7-diolpolyethoxylate) is included at 0.001 weight parts in 100 weight parts in total. The surfactant in Kanda is calculated to be included at 0.0125 weight parts with respect to 100 weight parts of the resin (polyvinyl alcohol). The lower limit of the content of the surfactant in claim 29 is 100 times more than Kanda et al. Thus, claim 29 is not obvious over the combination of the references.

As to newly added claim 30, none of the cited references teaches any specific content of the surfactant in order to efficiently thicken a resist pattern formed by using an ArF resist.

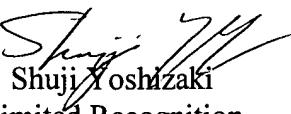
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(3) In view of the aforementioned amendments and accompanying remarks, Applicants submit that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned representative at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,  
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Attachment: Limited Recognition  
Petition for Extension of Time  
Amendment Transmittal